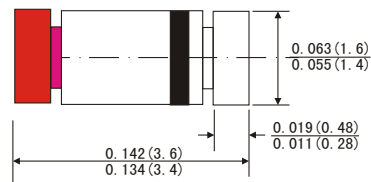


FEATURES

- Metal-on-silicon junction
- Low turn-on voltage
- Ultrafast switching speed
- Primarily intended for high level UHF detection and pulse applications with broad dynamic range
- The diode is also available in the DO-35 case with type designation BAT45
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MiniMELF



MECHANICAL DATA

- Case: MiniMELF glass case(SOD-80)
- Weight: Approx. 0.05 gram

Dimensions in inches and (millimeters)

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V _{RRM}	15	V
Surge non repetitive Forward current t _p ≤1S	I _{FSM}	2.0	A
Forward Continuous Current	I _F	30	mA
Operation and storage temperature range	T _A /T _{STG}	-65 to+150	°C

ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

	Symbols	Min.	Typ.	Max.	Units
Reverse breakover voltage at I _R =10μA	V _R	15			V
Leakage current at V _R =6V	I _R			100	nA
Forward voltage drop at I _F =1mA	V _F			0.38	V
Test pulse: t _p ≤300μs δ <2%	I _F =10mA			0.5	V
	I _F =30mA			1	V
Junction Capacitance at V _R =1V, f=1MHz	C _J			1.1	pF
Thermal resistance	R _{θJA}			400	K/W

RATINGS AND CHARACTERISTIC CURVES LL45

Figure 1. Forward current versus forward voltage at different temperatures (typical values)

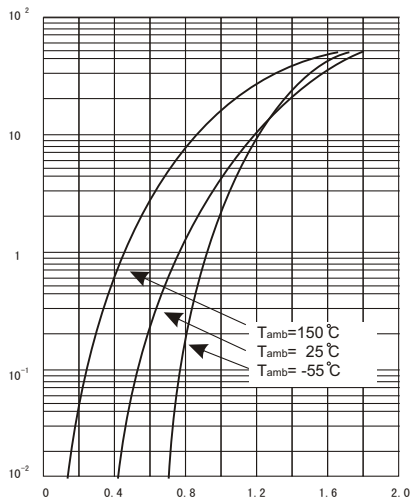


Figure 2. Capacitance C_J versus reverse applied voltage V_R (typical values)

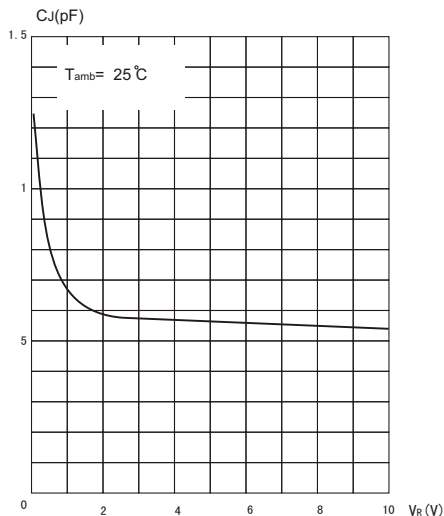


Figure 3. Reverse current versus ambient temperature

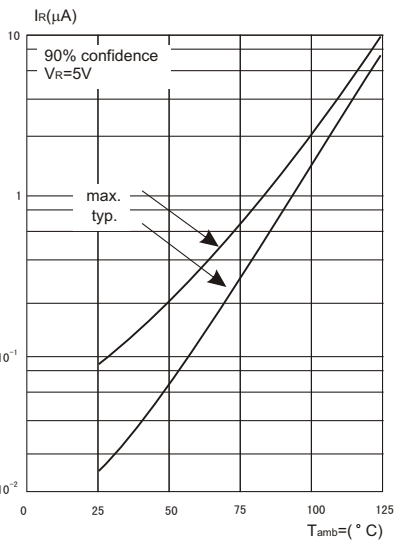


Figure 4. Reverse current versus continuous reverse voltage (typical values)

